

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



DMN61D9UW

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ V _{GS} = 5.0V	340mA
607	2.5Ω @ V _{GS} = 2.5V	300mA

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

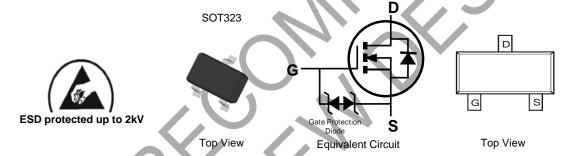
- Motor controls
- Power management functions
- backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMN61D9UWQ)

Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



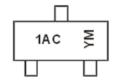
Ordering Information (Note 4)

Part Number	Package	Packing		
Part Number	Package	Qty.	Carrier	
DMN61D9UW-7	SOT323	3,000	Tape & Reel	
DMN61D9UW-13	SOT323	10,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1AC= Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	С		J	K	L	М	N	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit		
Drain-Source Voltage		VDSS	60	V		
Gate-Source Voltage			V_{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 5.0V	Steady State	T _A = +25°C T _A = +70°C	l _D	340 270	mA	
Continuous Diam Current (Note 6) VGS = 5.0V	t<5s	$T_A = +25$ °C $T_A = +70$ °C	lo	400 300	mA	
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	0.4	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%) (Note 6	5)	I _{DM}	1.2	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	320	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Pau	393	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	R _θ ЈА	306	C/W	
Total Power Dissipation (Note 6)		PD	440	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Pau	289	°C/W	
Thermal Resistance, Junction to Ambient (Note o)	t<5s	Reja	235	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

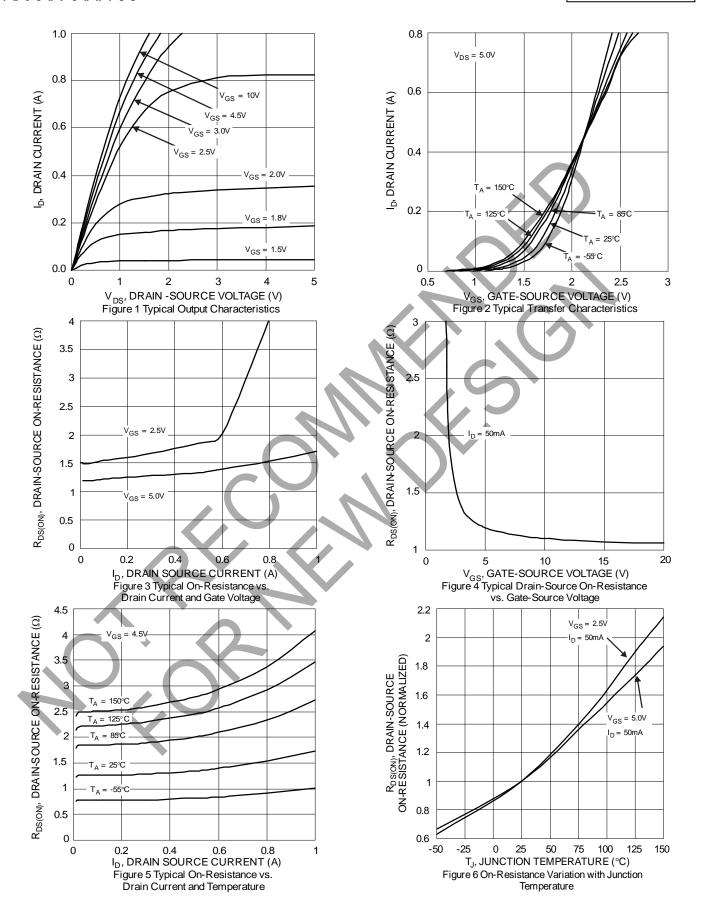
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	1		1.0	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	Igss	_		±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)			Ť			
Gate Threshold Voltage	Vgs(th)	0.5	_	1.0	>	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 5.0V, I_D = 0.05A$
Static Drain-Source On-Resistance	RDS(ON)	_	1.6	2.5	Ω	$V_{GS} = 2.5V, I_{D} = 0.05A$
			2.5	3.5		$V_{GS} = 1.8V, I_{D} = 0.05A$
Forward Transconductance	Yfs	200			mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}	_	0.75	1.4	V	V _G S = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)	·					
Input Capacitance	Ciss		28.5		рF	V 00V V 0V
Output Capacitance	Coss		3.9	_	рF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.5	_	рF	1 = 1.0IVII 12
Gate Resistance	Rg		65	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	_	0.4	_	nC	\\ 45\\ \\ 40\\
Gate-Source Charge	Qgs	_	0.1	_	nC	Vgs = 4.5V, Vps = 10V, Ip = 250mA
Gate-Drain Charge	Q_{gd}	_	0.1	_	nC	ID = 250MA
Turn-On Delay Time	tD(ON)	_	2.1	_	ns	
Turn-On Rise Time	t _R	_	1.8	_	ns	V _{DD} = 30V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	_	14.4	_	ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time	tF	_	8.4	_	ns	

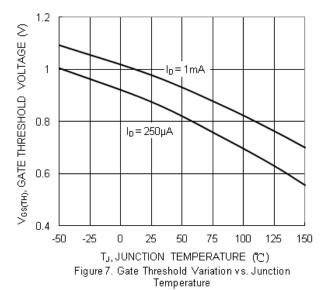
Notes:

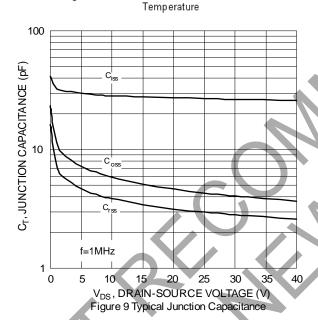
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

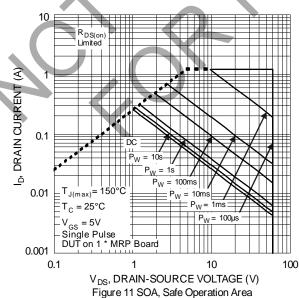


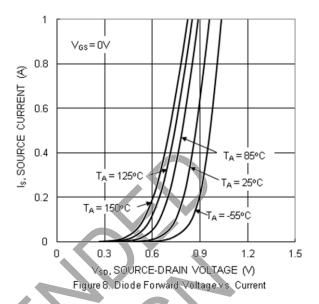


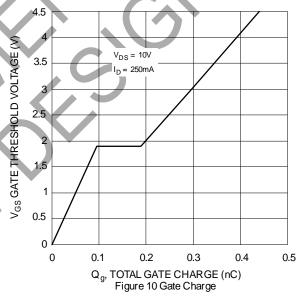




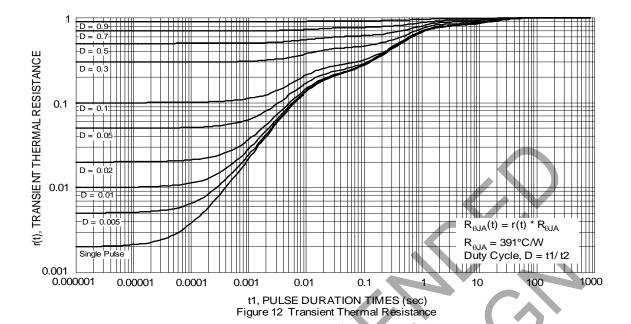










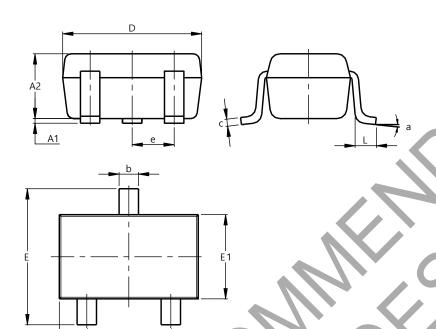




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

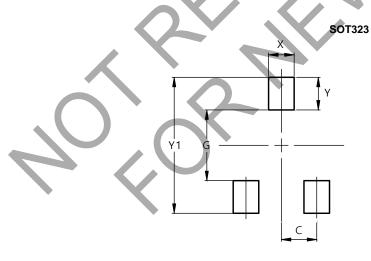
SOT323



SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E	1.15	1.35	1.30					
е	7).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500



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